

# Yota Takamura

## List of Publications by Year in descending order

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25  
papers

415  
citations

1040056

9  
h-index

713466

21  
g-index

25  
all docs

25  
docs citations

25  
times ranked

532  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of L21-ordering in full-Heusler Co <sub>2</sub> FeSi alloy thin films formed by rapid thermal annealing. Journal of Applied Physics, 2009, 105, .	2.5	127
2	Probe of spin dynamics in superconducting NbN thin films via spin pumping. Physical Review B, 2018, 97, .	3.2	49
3	Quantitative analysis of atomic disorders in full-Heusler Co <sub>2</sub> FeSi alloy thin films using x-ray diffraction with Co <sup>K<math>\alpha</math></sup> and Cu <sup>K<math>\alpha</math></sup> sources. Journal of Applied Physics, 2010, 107, .	2.5	43
4	Full-Heusler Co <sub>2</sub> FeSi alloy thin films with perpendicular magnetic anisotropy induced by MgO-interfaces. Journal of Applied Physics, 2014, 115, .	2.5	37
5	Characterization of half-metallic L21-phase Co <sub>2</sub> FeSi full-Heusler alloy thin films formed by rapid thermal annealing. Journal of Applied Physics, 2008, 103, .	2.5	25
6	Large Enhancement of Critical Current in Superconducting Devices by Gate Voltage. Nano Letters, 2021, 21, 216-221.	9.1	21
7	Magnetic anisotropy of [Co <sub>2</sub> MnSi/Pd] <sub>n</sub> superlattice films prepared on MgO(001), (110), and (111) substrates. Applied Physics Letters, 2015, 106, .	3.3	17
8	Formation of Co <sub>2</sub> FeSi/SiO <sub>x</sub> N <sub>y</sub> /Si tunnel junctions for Si-based spin transistors. Journal of Applied Physics, 2010, 107, 09B104.	2.5	9
9	Epitaxial germanidation of full-Heusler Co <sub>2</sub> FeGe alloy thin films formed by rapid thermal annealing. Journal of Applied Physics, 2011, 109, 07B768.	2.5	9
10	Fabrication of High-Quality Co <sub>2</sub> FeSi/SiO <sub>x</sub> N <sub>y</sub> /Si(100) Tunnel Contacts Using Radical-Oxynitridation-Formed SiO <sub>x</sub> N <sub>y</sub> Barrier for Si-Based Spin Transistors. Journal of Electronic Materials, 2012, 41, 954-958.	2.2	9
11	Methods to induce perpendicular magnetic anisotropy in full-Heusler Co <sub>2</sub> FeSi thin layers in a magnetic tunnel junction structure. AIP Advances, 2018, 8, .	1.3	9
12	Switchable Josephson junction based on interfacial exchange field. Applied Physics Letters, 2019, 114, 022601.	3.3	9
13	Analysis of Hanle-effect signals observed in Si-channel spin accumulation devices. Journal of Applied Physics, 2014, 115, 17C307.	2.5	8
14	Formation of Si- and Ge-based Full-Heusler Alloy Thin Films using SOI and GOI Substrates for the Half-metallic Source and Drain of Spin Transistors. ECS Transactions, 2009, 16, 945-952.	0.5	7
15	Analysis and control of the Hanle effect in metal-oxide-semiconductor inversion channels. Journal of Applied Physics, 2012, 111, 07C323.	2.5	7
16	Analysis and Design of Hanle-Effect Spin Transistors at 300 K. IEEE Magnetics Letters, 2011, 2, 3000404-3000404.	1.1	6
17	Compact magneto-optical isolator with cobalt ferrite on silicon photonic circuits. Applied Physics Express, 2015, 8, 082201.	2.4	6
18	Analysis and design of nonlocal spin devices with electric-field-induced spin-transport acceleration. Journal of Applied Physics, 2015, 117, 17D919.	2.5	4

#	ARTICLE	IF	CITATIONS
19	Spin accumulation in Si channels using CoFe/MgO/Si and CoFe/AlO <sub>x</sub> /Si tunnel contacts with high quality tunnel barriers prepared by radical-oxygen annealing. Journal of Applied Physics, 2015, 117, 17B531.	2.5	3
20	Manipulation of the Magnetic Properties of Co <sup>2+</sup> and Fe <sup>2+</sup> Doped Layered Titanates by Alkyl Ammonium Intercalation. Advanced Materials Interfaces, 2016, 3, 1600509.	3.7	3
21	Fabrication and characterization of spin injector using a high-quality B2-ordered-Co <sub>2</sub> FeSi <sub>0.5</sub> Al <sub>0.5</sub> /MgO/Si(100) tunnel contact. Journal of Applied Physics, 2015, 117, 17D151.	2.5	2
22	Inverse-magnetostriction-induced switching current reduction of STT-MTJs and its application for low-voltage MRAM. Solid-State Electronics, 2017, 128, 194-199.	1.4	2
23	Field-Effect Spin-Transistors. , 2016, , 1243-1279.		2
24	Spin-orbit torque magnetization switching in a perpendicularly magnetized full Heusler alloy Co <sub>2</sub> FeSi. AIP Advances, 2021, 11, .	1.3	1
25	Devices and Applications: Spin Transistors and Spin Logic Devices. , 2014, , 1-31.		0